

Substitute form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet	A1	of	A1
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Complete if Known	10/525442
To Be Assigned	

Application Number	To Be Assigned
Filing Date	Concurrently Herewith
First Named Inventor	Takahashi
Group Art Unit	To Be Assigned
Examiner Name	Unknown
Attorney Docket Number	5576-177

U.S. PATENTS AND PATENT PUBLICATIONS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	3.	Takahashi et al., "New vapor phase deposition of pyrite thin films using FeCl_3 and CH_3CSNH_2 ", <i>Journal of Materials Science Letters</i> 19:2223-2224 (2000)	
	4.	Takahashi et al., "Preparation of pyrite thin films by atmospheric pressure chemical vapor deposition using FeCl_3 and CH_3CSNH_2 ", <i>Journal of Materials Chemistry</i> 10:2346-2348 (2000)	
	5.	Lichtenberger et al., "Structural optical and electrical properties of polycrystalline iron pyrite layers deposited by reactive d. c. magnetron sputtering", <i>Thin Solid Films</i> 246.6-12 (1994)	
	6.	Höpfner et al., "Stoichiometry-, phase- and orientation-controlled growth of polycrystalline pyrite (FeS_2) thin films by MOCVD", <i>Journal of Crystal Growth</i> 151:325-334 (1995)	
	7.	International Search Report corresponding to PCT/JP03/010814 mailed on December 9, 2003.	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /E.B./

Examiner Signature	/Elizabeth Burkhart/	Date Considered	08/25/2008
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.